			DB	Time stamp
L Number	Hits	Search Text	USPAT;	2003/05/01 20:30
17	246233	resistor		2003/03/01 23:30
			US-PGPUB	2003/05/01 20:30
18	105089	resistor and gate	USPAT;	2003/03/01 20.30
"			US-PGPUB	0000/05/01 30:30
19	77302	(resistor and gate) and (via contact hole	USPAT;	2003/05/01 20:30
+ 7		recess trench)	US-PGPUB	2222 /05 /01 20 20
20	36105	((resistor and gate) and (via contact	USPAT;	2003/05/01 20:30
20	30200	hole recess trench)) and (semiconductor	US-PGPUB	
		substrate wafer)		(05 (05 00 30
21	32549	(((resistor and gate) and (via contact	USPAT;	2003/05/01 20:30
21	32013	hole recess trench)) and (semiconductor	US-PGPUB	
		substrate wafer)) and (source drain)		
23	352	((((resistor and gate) and (via contact	USPAT	2003/05/01 19:28
23	002	hole recess trench)) and (semiconductor		
		substrate wafer)) and (source drain)) and		
		((dummy sacrificial temporary) near5 gate)		
22	28870	(((resistor and gate) and (via contact	USPAT	2003/05/01 19:39
22	20070	hole recess trench)) and (semiconductor		
		substrate wafer)) and (source drain)		
24	2273	((((resistor and gate) and (via contact	USPAT	2003/05/01 19:48
2 1		hole recess trench) and (semiconductor		1
		substrate wafer)) and (source drain)) and		
		438/\$.ccls.		
25	244923	resistor	EPO; JPO;	2003/05/01 20:30
25			DERWENT;	
			IBM_TDB	
26	23288	resistor and gate	EPO; JPO;	2003/05/01 20:30
20			DERWENT;	
			IBM_TDB	
27	6955	(resistor and gate) and (via contact hole	EPO; JPO;	2003/05/01 20:30
- '		recess trench)	DERWENT;	
			IBM_TDB	
28	1553	((resistor and gate) and (via contact	EPO; JPO;	2003/05/01 20:30
20		hole recess trench)) and (semiconductor	DERWENT;	
		substrate wafer)	IBM_TDB	
29	909		EPO; JPO;	2003/05/01 20:31
123		hole recess trench)) and (semiconductor	DERWENT;	
		substrate wafer)) and (source drain)	IBM_TDB	